



70V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25 ℃	
-70V	160mΩ @ V _{GS} = -10V	-2.6A	
-70V	250mΩ @ V _{GS} = -4.5V	-1.6A	

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

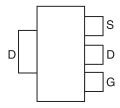
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208³
- Weight: 0.112 grams (Approximate)

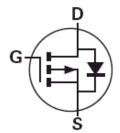
SOT223



Top View



Pin Out - Top View



Equivalent Circuit

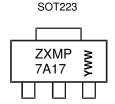
Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
ZXMP7A17GTA	Commercial	SOT223	1,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMP7A17 = Product Type Marking Code YWW_ = Date Code Marking Y or Y = Last Digit of Year (ex: 5= 2015) WW or WW = Week Code (01~53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic Drain-Source Voltage Gate-Source Voltage		Symbol	Value	Unit V	
		V_{DSS}	-70		
			V_{GS}	±20	V
		(Note 6)		-3.7	
Continuous Drain Current	$V_{GS} = -10V$	T _A = +70 °C (Note 6)	I _D	-2.9	Α
		(Note 5)		-2.6	
Pulsed Drain Current	V _{GS} = -10V	(Note 7)	I _{DM}	-9.6	Α
Continuous Source Current	(Body Diode)	(Note 6)	I _S	-4.8	Α
Pulsed Source Current (Bod	y Diode)	(Note 7)	I _{SM}	-9.6	Α

Thermal Characteristics (@TA = +25 ℃, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		2.0 16.0	W	
Linear Derating Factor	(Note 6)	P _D	3.9 31	mW/℃	
Thermal Resistance, Junction to Ambient	(Note 5)	В	62.5	°C/W	
Thermal nesistance, Junction to Ambient	(Note 6)	R _{0JA}	34	G/VV	
Operating and Storage Temperature Range		T_{J}, T_{STG}	-55 to +150	∞	

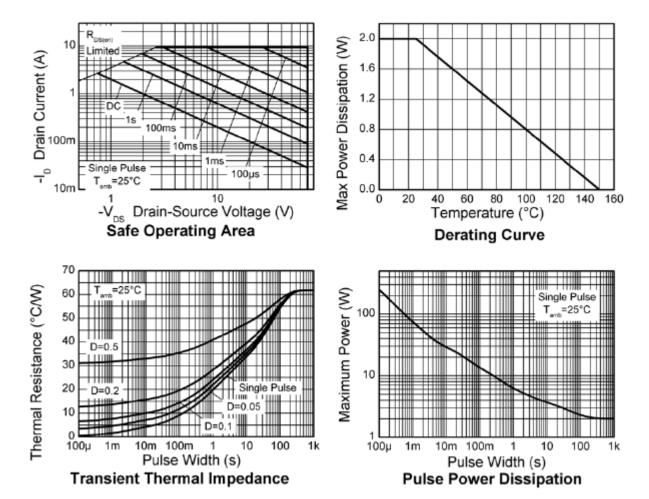
Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV_{DSS}	-70	_	_	V	$I_D = -250 \mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μΑ	V _{DS} = -70V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}		—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS					•		
Gate Threshold Voltage	V _{GS(th)}	-1.0	_	_	V	I_{D} = -250 μ A, V_{DS} = V_{GS}	
Static Drain Source On Begintance (Note 9)				0.16	Ω	V _{GS} = -10V, I _D = -2.1A	
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	_	_	0.25	12	V _{GS} = -4.5V, I _D = -1.7A	
Forward Transconductance (Notes 8 & 9)	g _{fs}		4.4	_	S	V _{DS} = -15V, I _D = -2.1A	
Diode Forward Voltage (Note 8)	V_{SD}		-0.85	-0.95	V	I _S = -2.0A, V _{GS} = 0V	
Reverse recovery time (Note 9)	t _{rr}		29.8	_	ns	I _S = -2.1A, di/dt= 100A/μs	
Reverse recovery charge (Note 9)	Q_{rr}		38.5	_	nC		
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	635	_	pF	., ., ., ., ., .,	
Output Capacitance	Coss	_	52		pF	V _{DS} = -40V, V _{GS} = 0V f= 1MHz	
Reverse Transfer Capacitance	C_{rss}	_	42.5	_	pF		
Total Gate Charge (Note 10)	Qg	_	9.6	_	nC	V _{GS} = -5V	
Total Gate Charge (Note 10)	Qq		18	_	nC	V _{DS} = -35V	
Gate-Source Charge (Note 10)	Q_{gs}		1.77	_	nC	V _{GS} = -10V	
Gate-Drain Charge (Note 10)	Q _{qd}		3.66	_	nC		
Turn-On Delay Time (Note 10)	t _{D(on)}		2.5	_	ns		
Turn-On Rise Time (Note 10)	tr	_	3.4	_	ns	V_{DD} = -35V, V_{GS} = -10V I_{D} = -1A, $R_{G} \cong 6.0 \Omega$	
Turn-Off Delay Time (Note 10)	$t_{D(off)}$	_	27.9		ns		
Turn-Off Fall Time (Note 10)	t _f	_	8		ns		

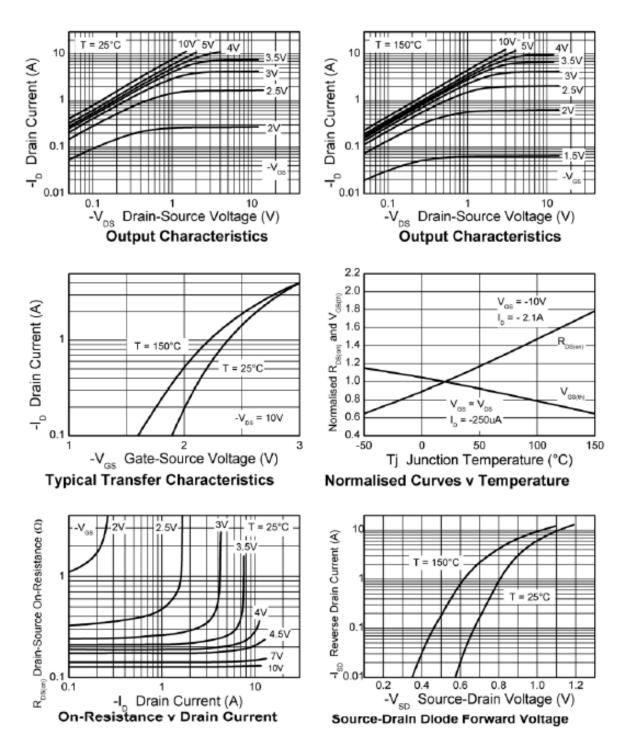
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note 5, except the device is measured at $t \le 5$ seconds.
- 7. Same as Note 5, except the device is pulsed with D= 0.05 and pulse width 10µs. The pulse current is limited by the maximum junction temperature.
- 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%.$
- 9. For design aid only, not subject to production testing.
- 10. Switching characteristics are independent of operating junction temperatures.

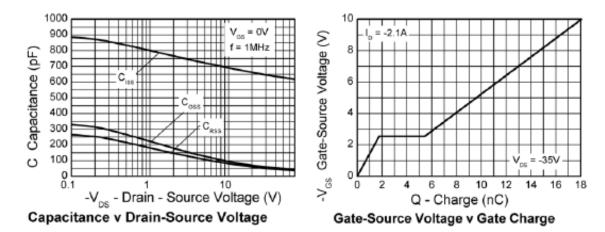






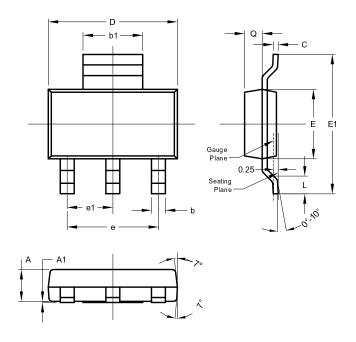






Package Outline Dimensions

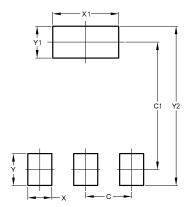
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
X	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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